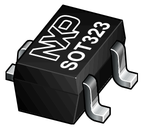


NX138BKW

60 V, N-channel Trench MOSFET

15 June 2016 | Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

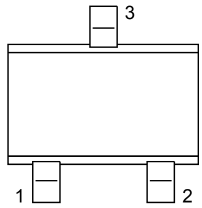
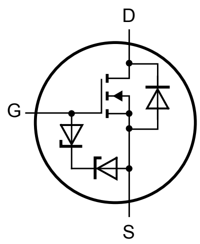
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C	[1]	-	-	210	mA
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 200 mA; T_j = 25 °C		-	2.1	3.5	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm^2.

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SC-70 (SOT323)	 017aaa255
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX138BKW	SC-70	plastic surface-mounted package; 3 leads	SOT323

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
NX138BKW	B8%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C	[1]	-	210	mA
		V_{GS} = 10 V; T_{amb} = 100 °C	[1]	-	135	mA
		V_{GS} = 10 V; T_{sp} = 25 °C		-	330	mA
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; t_p ≤ 10 µs		-	855	mA
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	266	mW
			[1]	-	321	mW
		T_{sp} = 25 °C		-	1.33	W
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{amb} = 25 °C	[1]	-	210	mA

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm^2.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

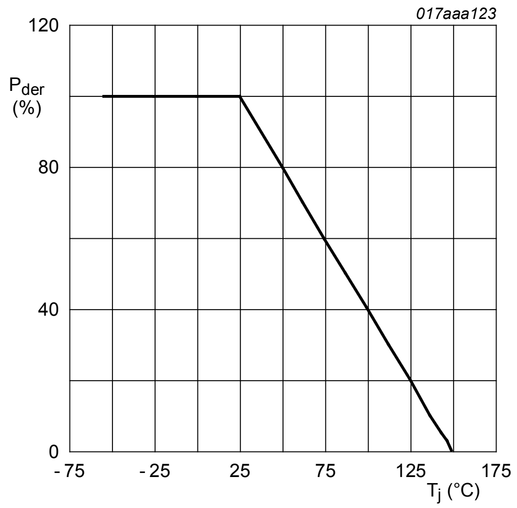


Fig. 1. **Normalized total power dissipation as a function of junction temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

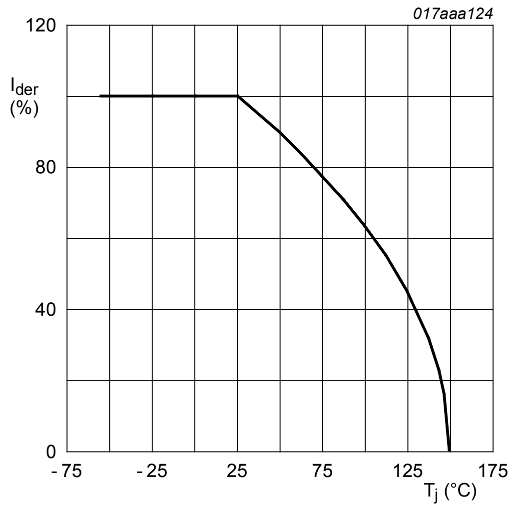
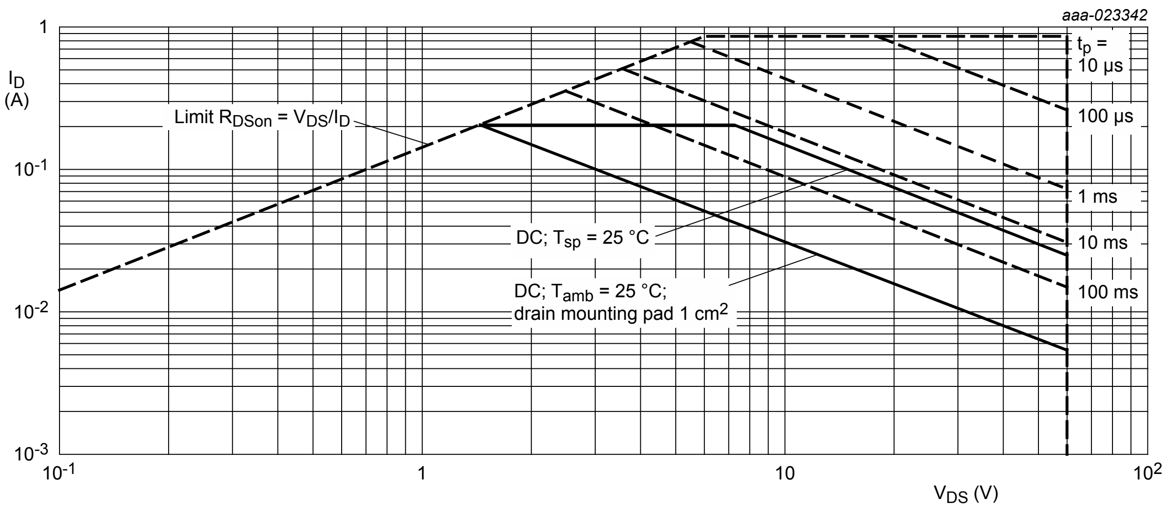


Fig. 2. **Normalized continuous drain current as a function of junction temperature**

$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$



I_{DM} = single pulse

Fig. 3. **Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage**

9. Thermal characteristics

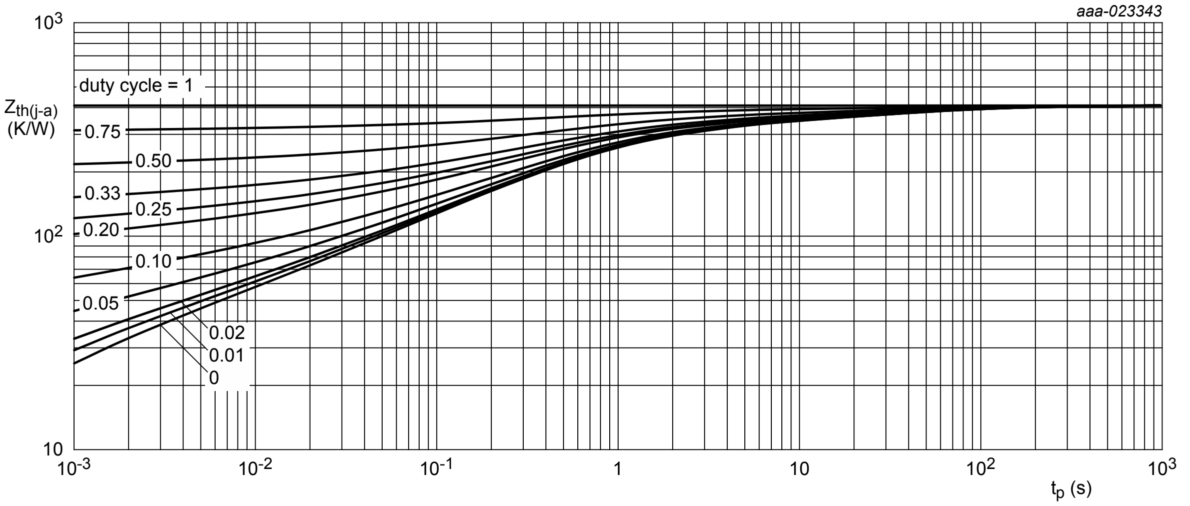
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	410	470	K/W
			[2]	-	340	390	K/W

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	75	85	K/W

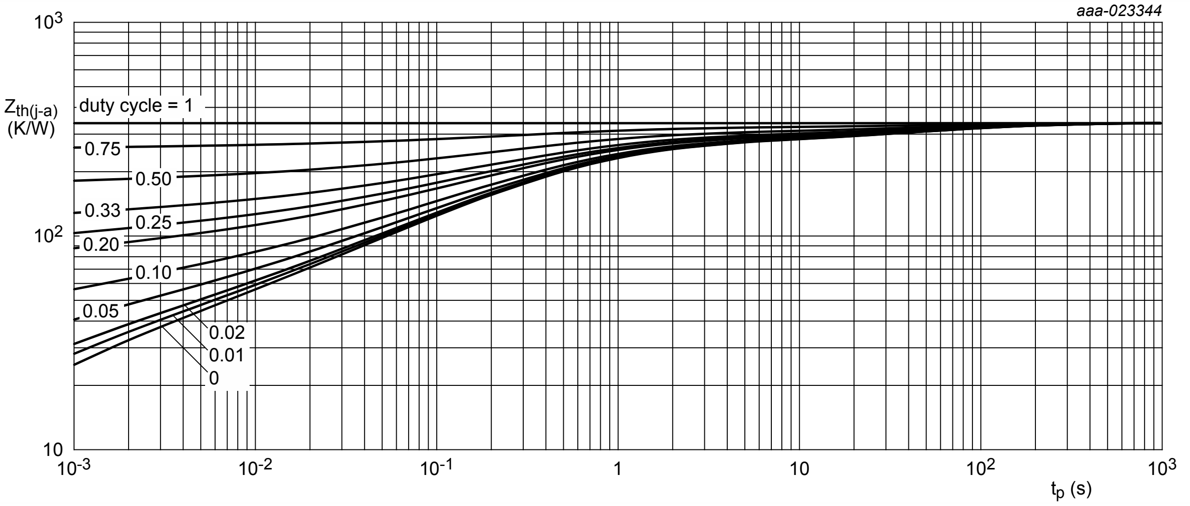
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm^2.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



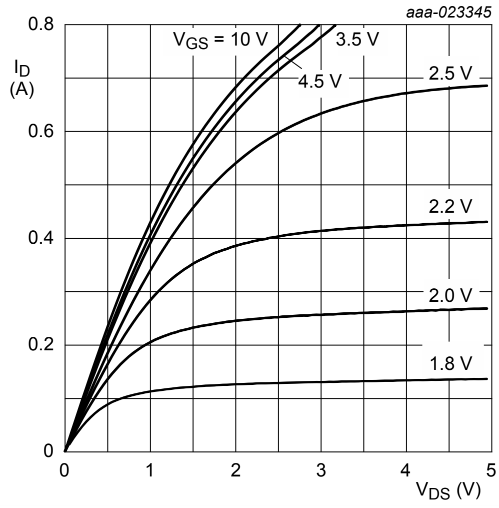
FR4 PCB, mounting pad for drain 1 cm^2

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

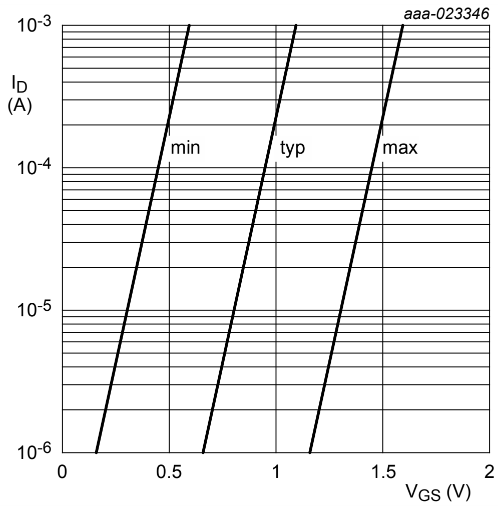
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		60	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS}=V_{GS}; T_j = 25 °C		0.5	1	1.5	V
I_{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	10	µA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-10	µA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C		-	-	1	µA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-1	µA
		V_{GS} = 5 V; V_{DS} = 0 V; T_j = 25 °C		-	-	0.3	µA
		V_{GS} = -5 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-0.3	µA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 200 mA; T_j = 25 °C		-	2.1	3.5	Ω
		V_{GS} = 10 V; I_D = 200 mA; T_j = 150 °C		-	4.3	7.2	Ω
		V_{GS} = 5 V; I_D = 170 mA; T_j = 25 °C		-	2.2	3.8	Ω
		V_{GS} = 2.5 V; I_D = 75 mA; T_j = 25 °C		-	2.6	5	Ω
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 200 mA; T_j = 25 °C		-	0.7	-	S
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	V_{DS} = 30 V; I_D = 200 mA; V_{GS} = 10 V; T_j = 25 °C		-	0.5	0.7	nC
Q_{GS}	gate-source charge			-	0.12	-	nC
Q_{GD}	gate-drain charge			-	0.12	-	nC
C_{iss}	input capacitance	V_{DS} = 30 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	20	-	pF
C_{oss}	output capacitance			-	3.1	-	pF
C_{rss}	reverse transfer capacitance			-	2	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; I_D = 200 mA; V_{GS} = 10 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C		-	8	12	ns
t_r	rise time			-	8	-	ns
$t_{d(off)}$	turn-off delay time			-	13	20	ns
t_f	fall time			-	5	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 200 mA; V_{GS} = 0 V; T_j = 25 °C		-	0.9	1.2	V



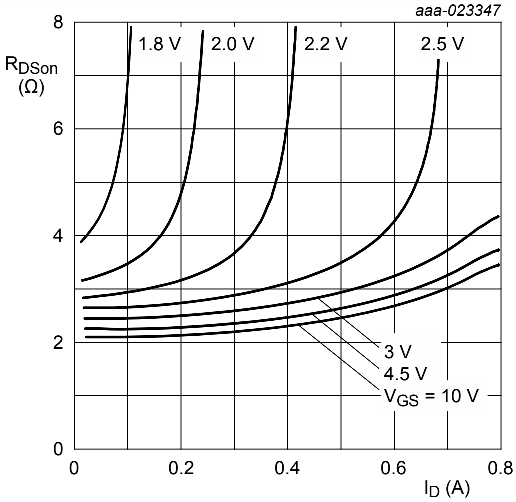
T_j = 25 °C

Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



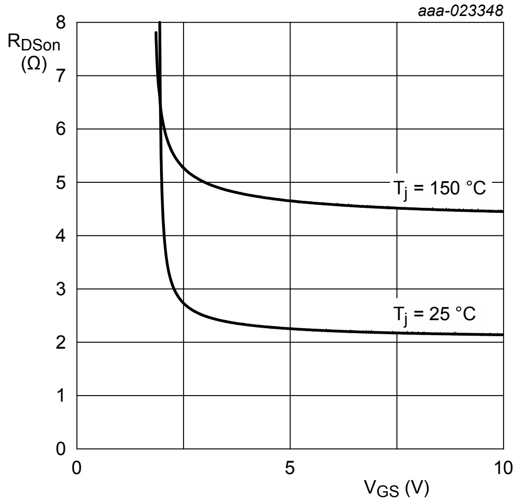
V_{DS} = 5 V
T_j = 25 °C

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



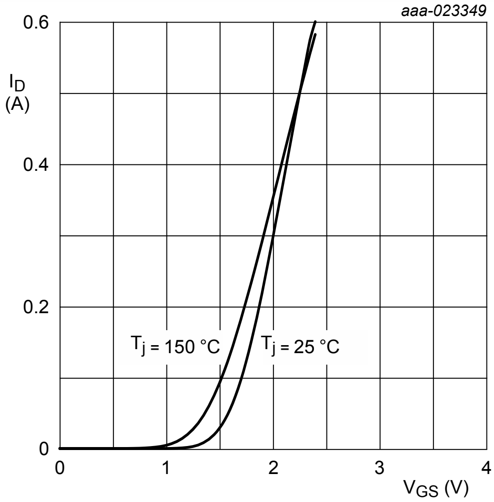
T_j = 25 °C

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



I_D = 0.2 A

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$V_{DS} > I_D \times R_{DSon}$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

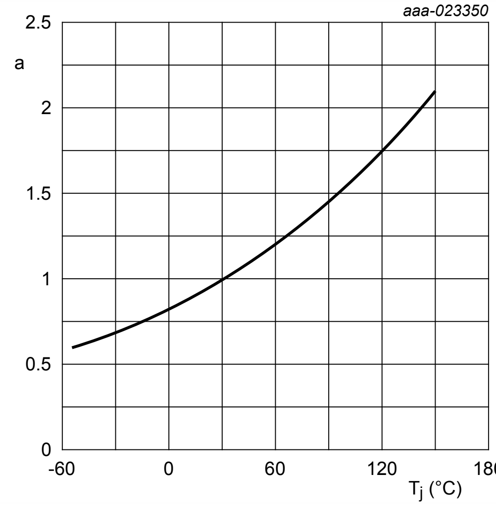
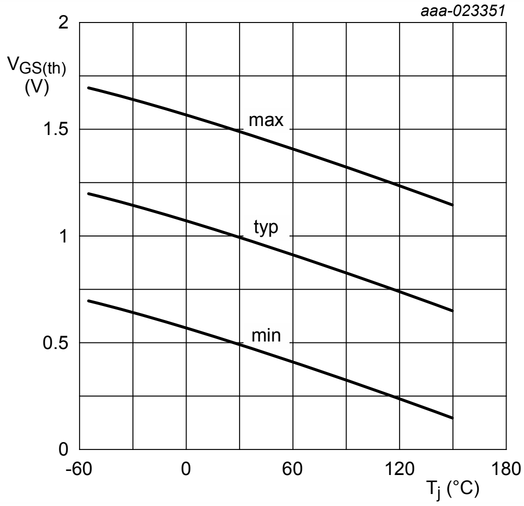


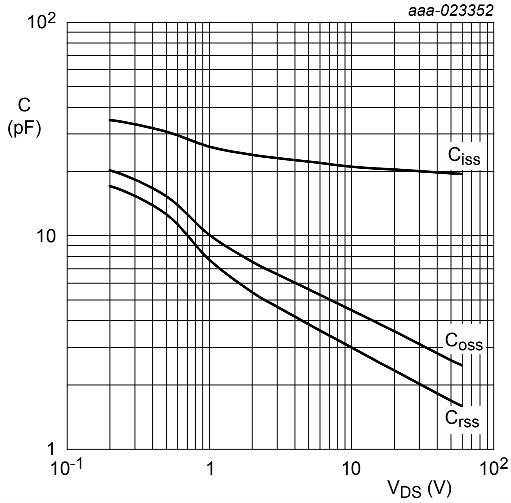
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$



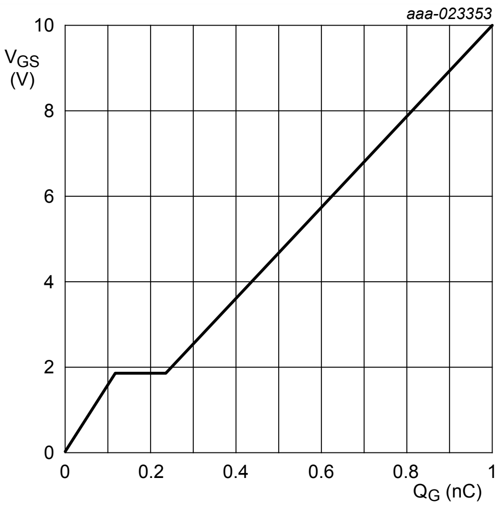
I_D = 250 µA; $V_{DS} = V_{GS}$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; V_{GS} = 0 V

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



V_{DS} = 30 V; I_D = 0.2 A

Fig. 14. Gate-source voltage as a function of gate charge; typical values

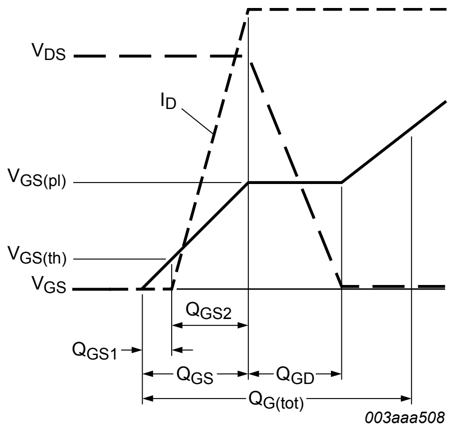
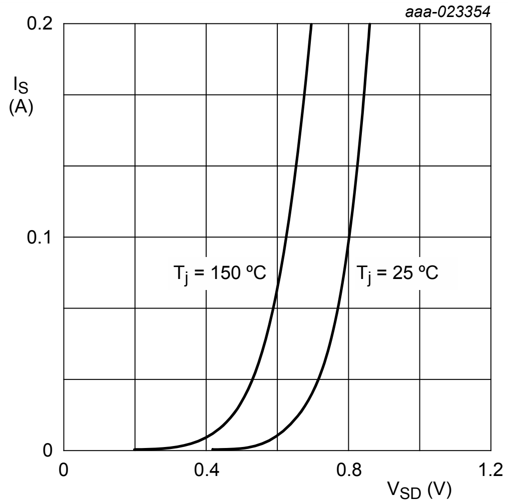


Fig. 15. MOSFET transistor: Gate charge waveform definitions



V_{GS} = 0 V

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

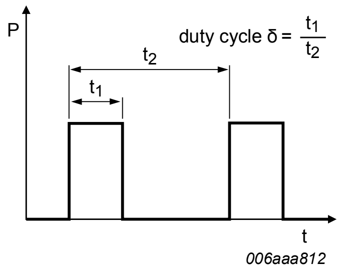
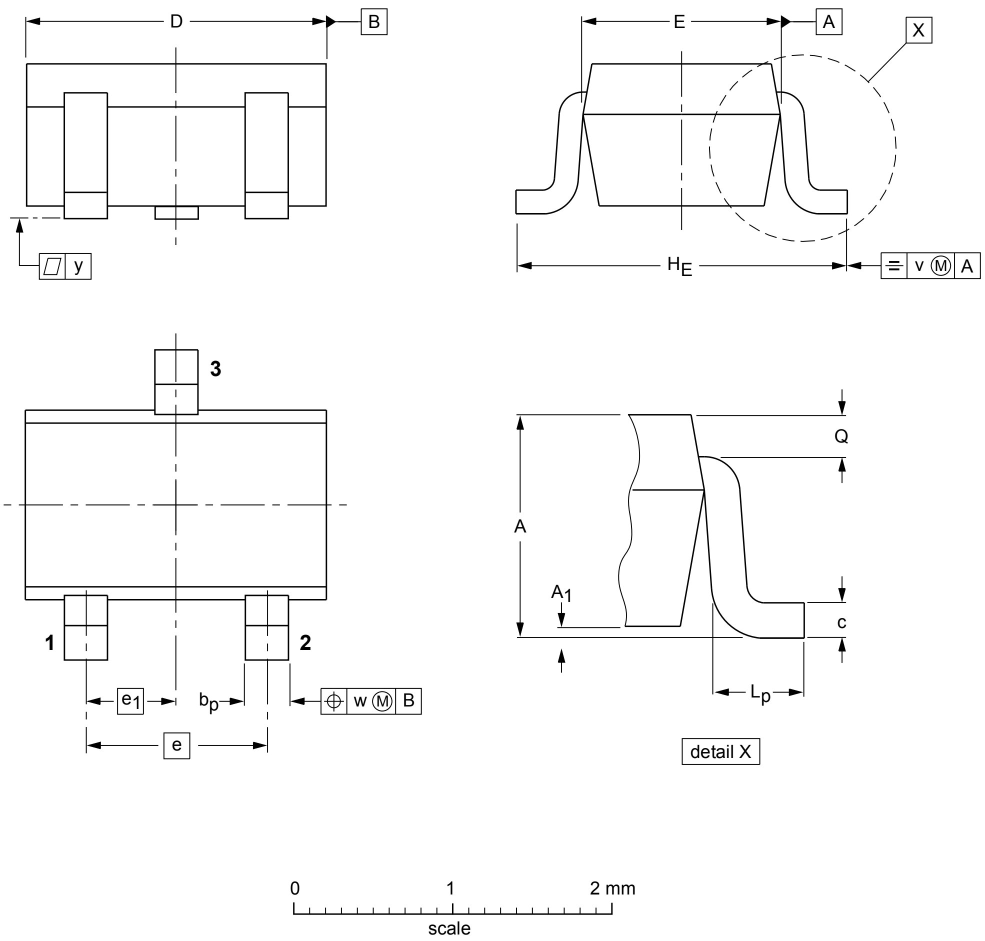


Fig. 17. Duty cycle definition

12. Package outline

Plastic surface-mounted package; 3 leads **SOT323**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT323			SC-70			04-11-04 06-03-16

Fig. 18. Package outline SC-70 (SOT323)

13. Soldering

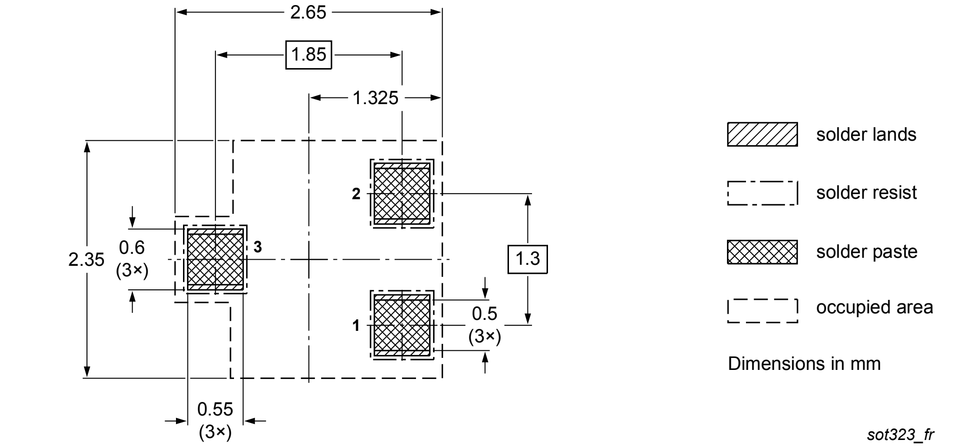


Fig. 19. Reflow soldering footprint for SC-70 (SOT323)

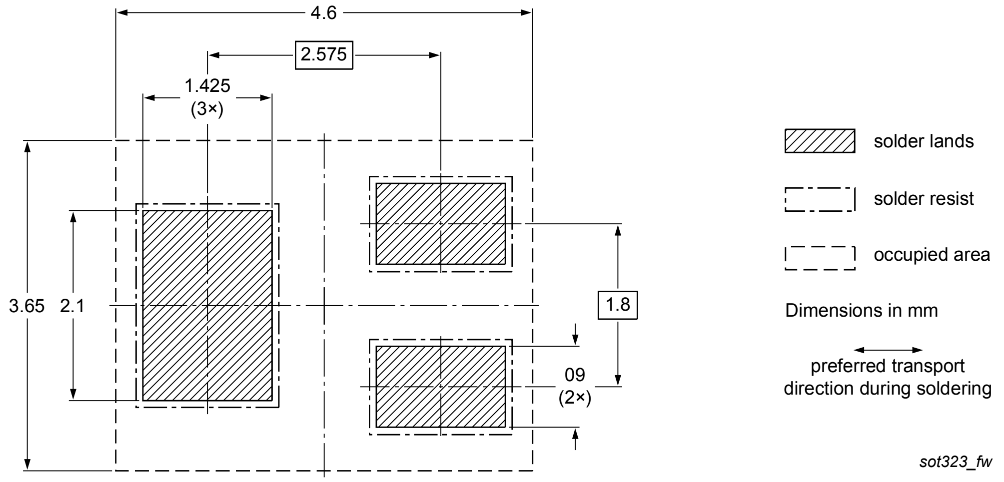


Fig. 20. Wave soldering footprint for SC-70 (SOT323)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX138BKW v.1	20160615	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Date of release: 15 June 2016